

## SEMITOP<sup>®</sup> 3

**IGBT** Module

### SK80GB063

Preliminary Data

### **Features**

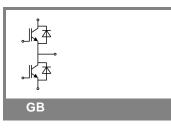
- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- High short circuit capability Low tail current with low
- temperature dependence
- Integrated PTC temperature sensor

### **Typical Applications\***

- Switching (not for linear use)Inverter
- Switched mode power supplies
- UPS

Absolut	e Maximum Ratings	Ts	= 25 °C, unless otherwise	specified	
Symbol	Conditions		Values		
IGBT					
V <sub>CES</sub>	T <sub>j</sub> = 25 °C		600	V	
I <sub>C</sub>	T <sub>j</sub> = 125 °C	T <sub>s</sub> = 25 °C	81	А	
		T <sub>s</sub> = 80 °C	57	А	
I <sub>CRM</sub>	I <sub>CRM</sub> = 2 x I <sub>Cnom</sub>		200	А	
V <sub>GES</sub>			± 20	V	
t <sub>psc</sub>	$V_{CC}$ = 300 V; $V_{GE} \le$ 20 V; VCES < 600 V	T <sub>j</sub> = 125 °C	10	μs	
Inverse	Diode				
I <sub>F</sub>	T <sub>j</sub> = 150 °C	T <sub>s</sub> = 25 °C	79	А	
		T <sub>s</sub> = 80 °C	53	А	
I <sub>FRM</sub>	I <sub>FRM</sub> = 2 x I <sub>Fnom</sub>		150	А	
I <sub>FSM</sub>	t <sub>p</sub> = 10 ms; half sine wave	T <sub>j</sub> = 150 °C	720	А	
Module					
I <sub>t(RMS)</sub>				А	
T <sub>vj</sub>			-40 +150	°C	
T <sub>stg</sub>			-40 +125	°C	
V <sub>isol</sub>	AC, 1 min.		2500	V	

Characteristics T <sub>s</sub> =			25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units	
IGBT							
V <sub>GE(th)</sub>	$V_{GE} = V_{CE}, I_C = 1,5 \text{ mA}$		4,5	5,5	6,5	V	
I <sub>CES</sub>	$V_{GE}$ = 0 V, $V_{CE}$ = $V_{CES}$	T <sub>j</sub> = 25 °C			0,3	mA	
		T <sub>j</sub> = 125 °C				mA	
I <sub>GES</sub>	V <sub>CE</sub> = 0 V, V <sub>GE</sub> = 30 V	T <sub>j</sub> = 25 °C			300	nA	
		T <sub>j</sub> = 125 °C				nA	
V <sub>CE0</sub>		T <sub>j</sub> = 25 °C		1		V	
		T <sub>j</sub> = 125 °C		1,1		V	
r <sub>CE</sub>	V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25°C		11		mΩ	
		T <sub>j</sub> = 125°C		9		mΩ	
V <sub>CE(sat)</sub>	I <sub>Cnom</sub> = 100 A, V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25°C <sub>chiplev.</sub>		2,1	2,5	V	
		T <sub>j</sub> = 125°C <sub>chiplev.</sub>		2	2,3	V	
C <sub>ies</sub>				4,3		nF	
C <sub>oes</sub>	$V_{CE}$ = 25, $V_{GE}$ = 0 V	f = 1 MHz				nF	
C <sub>res</sub>				0,4		nF	
Q <sub>G</sub>	V <sub>GE</sub> = 0 20 V			310		nC	
t <sub>d(on)</sub>				50		ns	
t <sub>r</sub>	$R_{Gon}$ = 10 $\Omega$	V <sub>CC</sub> = 300V		40		ns	
E <sub>on</sub>		I <sub>C</sub> = 100A		4		mJ	
t <sub>d(off)</sub>	$R_{Goff} = 10 \Omega$	$T_{j} = 125 ^{\circ}C$		300 35		ns	
t <sub>f</sub> E <sub>off</sub>		V <sub>GE</sub> =±15V		3		ns mJ	
R <sub>th(j-s)</sub>	per IGBT				0,6	K/W	





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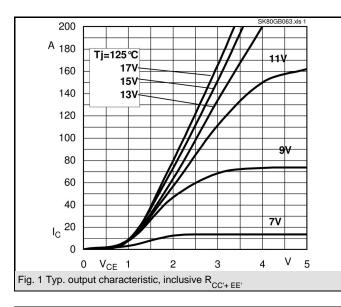
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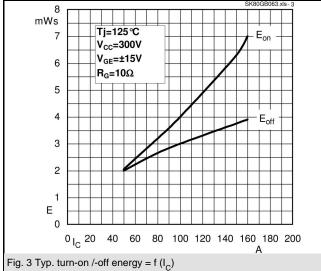
Characteristics							
Symbol	Conditions		min.	typ.	max.	Units	
Inverse D	liode						
$V_F = V_{EC}$	I <sub>Fnom</sub> = 60 A; V <sub>GE</sub> = 0 V	T <sub>j</sub> = 25 °C <sub>chiplev.</sub>		1,4		V	
		T <sub>j</sub> = 125 °C <sub>chiplev.</sub>		1,3		V	
V <sub>F0</sub>		T <sub>j</sub> = 125 °C		0,85	0,9	V	
r <sub>F</sub>		T <sub>j</sub> = 125 °C		6,5	11	mΩ	
I <sub>RRM</sub>	I <sub>F</sub> = 60 A	T <sub>i</sub> = 125 °C		90		Α	
Q <sub>rr</sub>	di/dt = -3000 A/µs			7		μC	
E <sub>rr</sub>	V <sub>CC</sub> = 300V			1,2		mJ	
R <sub>th(j-s)D</sub>	per diode				0,9	K/W	
M <sub>s</sub>	to heat sink M1		2,25		2,5	Nm	
w				30		g	

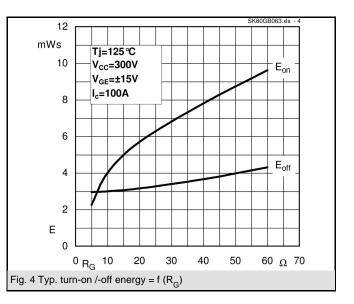
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

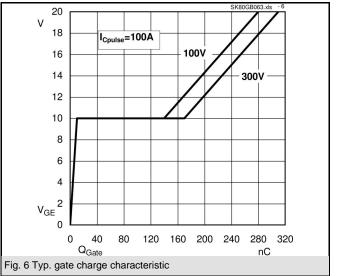
\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.





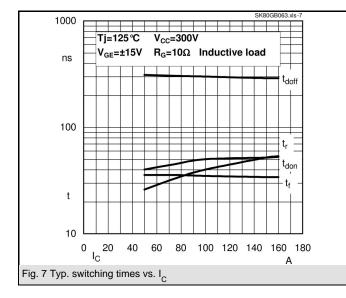


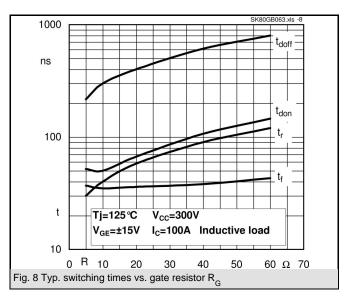


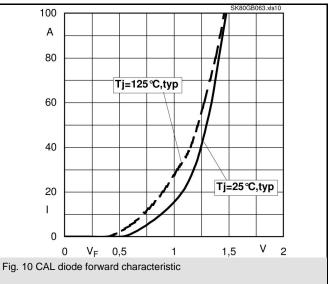


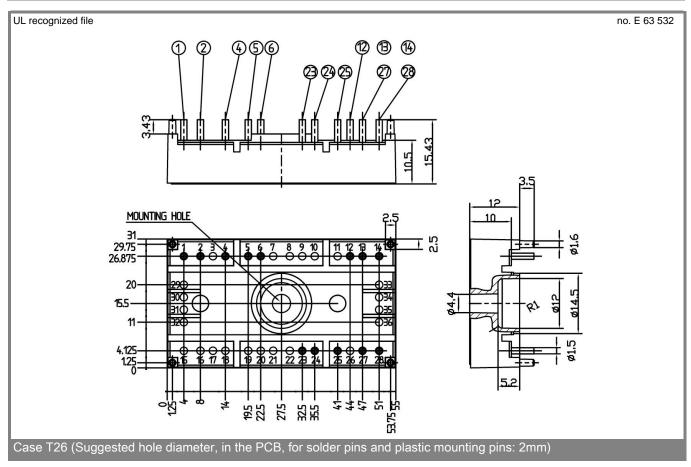
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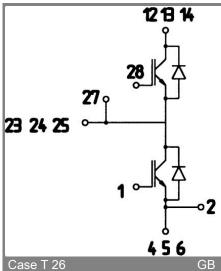
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